MGBR10S60C

DUAL MOS BARRIER RECTIFIER

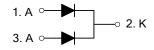
DESCRIPTION

The UTC **MGBR10S60C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

- * Super low forward voltage drop
- * High switching speed

■ SYMBOL

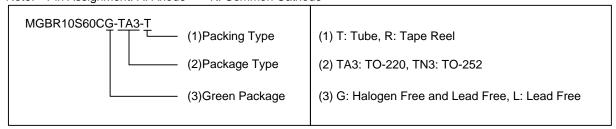


TO-220

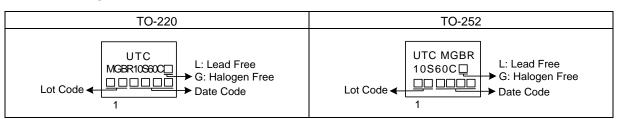
■ ORDERING INFORMATION

Ordering Number		Doolsone	Pin Assignment			Deelsing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR10S60CL-TA3-T	MGBR10S60CG-TA3-T	TO-220	Α	K	Α	Tube	
MGBR10S60CL-TN3-R	MGBR10S60CG-TN3-R	TO-252	Α	K	Α	Tape Reel	

Note: Pin Assignment: A: Anode K: Common Cathode



■ MARKING



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MGBR10S60C DIODE

■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	60	V
Working Peak Reverse Voltage		V_{RWM}	60	V
Peak Repetitive Reverse Voltage		V_{RRM}	60	V
Average Rectified Forward Current	Per Leg		5	Α
(Rated VR-20KHz Square Wave) – 50% duty cycle	Total	I _O	10	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I _{FSM}	150	А
Peak Repetitive Reverse Surge Current (2µS-1kHz)		I _{RRM}	2	Α
Operating Junction Temperature		T_J	-65~+150	°C
Storage Temperature		T _{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (PER LEG)

PARAMETER		SYMBOL	RATINGS	UNIT	
Lunction to Ambient	TO-220	0	62.5	°C/W	
Junction to Ambient	TO-252	θ_{JA}	110		
lumation to Cons	TO-220	0	2	°C/W	
Junction to Case	TO-252	θ _{JC}	2.5		

■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise specified.)

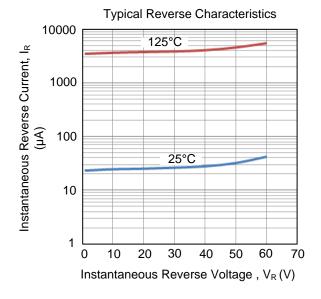
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.60mA	60			V
Forward Voltage Drop	V_{FM}	I _F =5A, T _J =25°C			0.53	V
		I _F =5A, T _J =125°C			0.48	V
Leakage Current (Note 1)	I _{RM}	V _R =60V, T _J =25°C			500	μA
		V _R =60V, T _J =125°C			50	mΑ

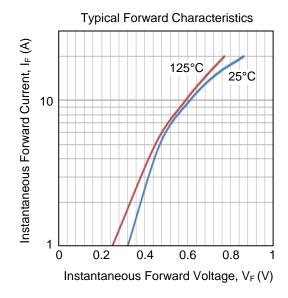
Notes: 1. Short duration pulse test used to minimize self-heating effect.

^{2.} Thermal resistance junction to case mounted on heatsink.

MGBR10S60C DIODE

■ TYPICAL CHARACTERISTICS





UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.